Silicon NPN Power Transistors 2SC1106

DESCRIPTION

- With TO-3 package
- High power dissipation
- High breakdown voltage

APPLICATIONS

- For voltage regulator ,inverter and switching mode power supply applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	350	V
V_{CEO}	Collector-emitter voltage	Open base	250	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		2	A
P_C	Collector power dissipation	T_C=25℃	80	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=0.1A ;I_B=0	250			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=1mA ;I_E=0	350			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ;I_C=0	6			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=1.5A; I_B=0.3A			5.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=1.5A; I_B=0.3A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=350V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=0.2A ; V_{CE}=5V	30			

PACKAGE OUTLINE

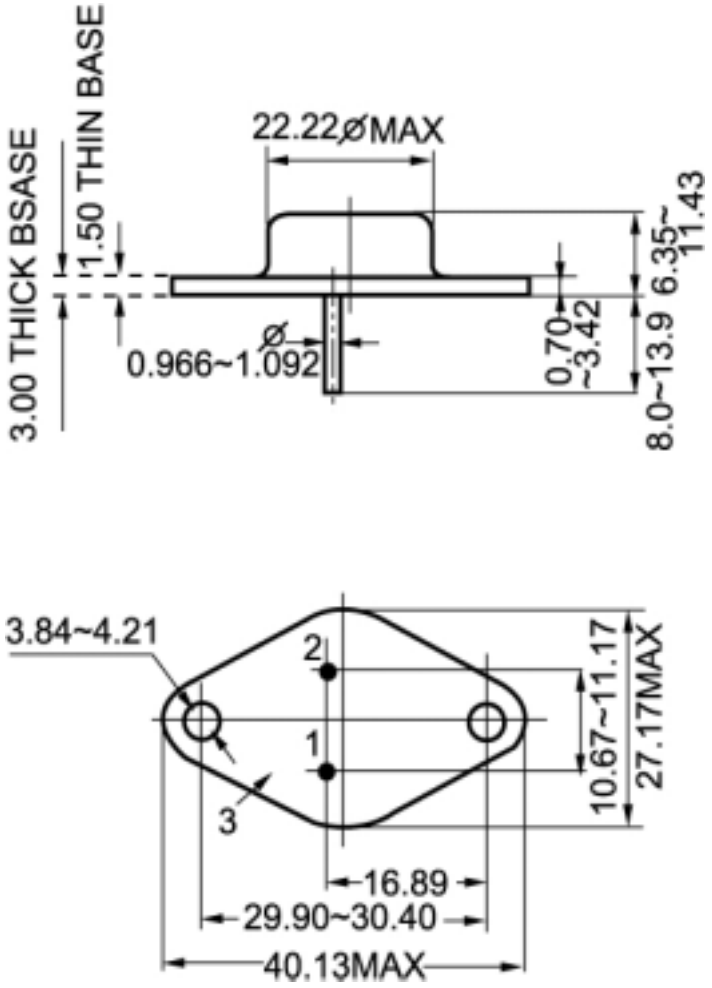

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)